

Please replace pg. 26, lines 17-27, with the amended paragraph below. A "marked-up" version of each amendment is including in **Attachment A**.

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In the event that the spray element is not programmed to spray, the topography positioned within the system may be replaced by another semiconductor topography as shown in step 66. The method may then continue through steps 61 and 64 as described above. Upon a time when the spray bar is programmed to spray, the method may continue to step 68 to spray a pressurized fluid from the spray element while continuing to move the polishing pad. Consequently, the method may include removing matter adhered to the polishing pad as shown in step 70. Either after or during steps 68 and 70, the polished topography may be replaced by another semiconductor topography. In this manner, the method of removing matter adhered to the polishing pad may be conducted while the polishing system is activated. In other words, the polishing system does not have to be shut down to remove matter adhered to the polishing pad.

Please replace pg. 29, lines 8-17, with the amended paragraph below. A "marked-up" version of each amendment is including in **Attachment A**.

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It will be appreciated to those skilled in the art having the benefit of this disclosure that this invention is believed to provide a method and a system for cleaning a polishing pad. Further modifications and alternative embodiments of various aspects of the invention will be apparent to those skilled in the art in view of this description. For example, the system as described herein may be applied to a polishing system which is adapted to polish a plurality of topographies. In addition, the system may be used for polishing a variety of materials, such as dielectric and conductive materials. It is intended that the following claims be interpreted to embrace all such modifications and changes and, accordingly, the drawings and the specification are to be regarded in an illustrative rather than a restrictive sense.

IN THE CLAIMS

Please cancel claims 2, 13, 15, 25, and 26 without prejudice or disclaimer as to the subject matter recited therein. Please replace claims 1, 3, 11, 12, 14, 16-18, 23, 24, and 27 with the amended claims below. A "marked-up" version of each amendment is including in **Attachment A**.

1. (Amended) A polishing system, comprising:

a polishing pad;

a spray element adapted to spray a pressurized fluid upon the polishing pad to remove matter adhered to the pad, wherein said matter is adhered to the polishing pad during a polishing process of a semiconductor topography, and wherein the spray element is configured to be arranged adjacent to an edge of the semiconductor topography which the polishing pad is moving away from during the polishing process; and

a dispense component adapted to dispense a polishing fluid onto the polishing pad during said polishing process, wherein the dispense component is configured to be arranged adjacent to an opposite edge of the semiconductor topography which the polishing pad is moving toward during the polishing process.

3. (Amended) The system of claim 1, wherein said matter comprises particles from the polishing fluid.

11. (Amended) A spray element adapted to be positioned within a polishing system and further adapted to remove matter adhered to a polishing pad of the system by spraying a pressurized fluid upon the polishing pad, wherein the spray element comprises a plurality of nozzles configured to spray the pressurized fluid and one or more adjustable shields arranged about the plurality of nozzles.

12. (Amended) The spray element of claim 11, wherein the spray element is adapted to be positioned within the polishing system such that the pressurized fluid is dispersed across a region extending across at least half of the width of the polishing pad.

14. (Amended) The spray element of claim 11, wherein a spray distribution from one of said plurality nozzles overlaps a spray distribution from an adjacent nozzle.

16. (Amended) The spray element of claim 11, wherein said shields are arranged along the sides of the spray element parallel to the projection of the nozzles.

17. (Amended) The spray element of claim 11, comprising a mounting structure with which to couple the spray element to the polishing system.

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18. (Amended) A method for cleaning a polishing pad, comprising:

moving the polishing pad relative to a spray element, wherein the spray element and polishing pad are positioned within a polishing system such that fluid openings of the spray element are positioned toward the polishing pad;

spraying a pressurized fluid in a pulsating sequence from the spray element upon the polishing pad during said moving; and

removing matter adhered to the polishing pad.

210
23. (Amended) A method for polishing multiple semiconductor topographies, comprising:

moving a polishing pad with respect to a semiconductor topography and a spray element;

polishing the semiconductor topography by positioning it against the moving polishing pad;

measuring an amount of matter adhered to the polishing pad subsequent to said polishing;

2
AL { spraying a pressurized fluid from the spray element upon the polishing pad while moving the polishing pad, wherein said spraying is conducted based upon the amount of matter measured; and

removing the matter adhered to the polishing pad.

24. (Amended) The method of claim 23, further comprising polishing one or more additional topographies prior to said measuring.

27. (Amended) The method of claim 18, wherein said spraying is conducted simultaneously with polishing one or more semiconductor topographies with the polishing system.
